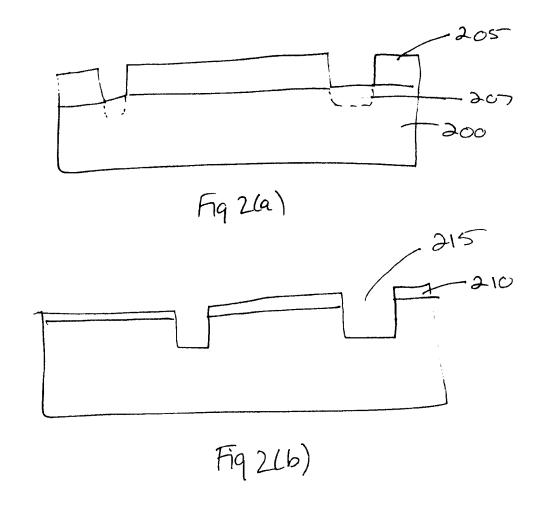
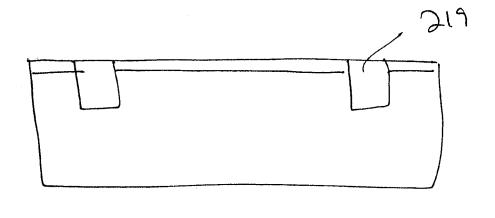


FIGURE 1

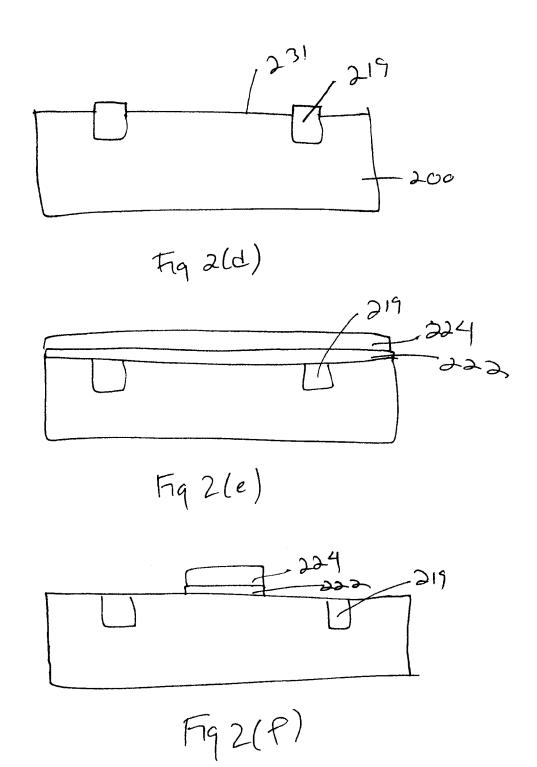
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Tag 2(c)

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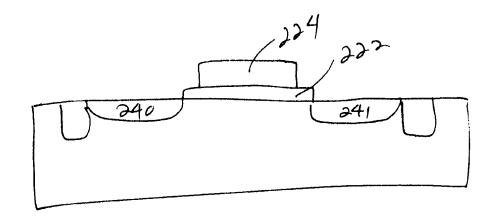


Fig. 26g)

Fig. 26g)

Fig. 26g)

Fig. 26g)

Fig. 26g)

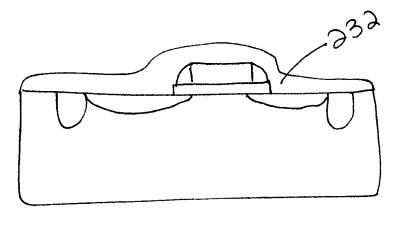
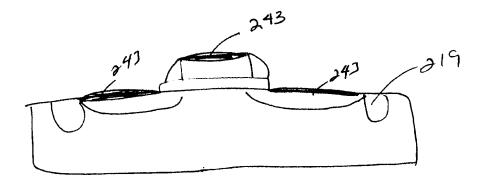


Fig 2(i)

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Tag 2/1)

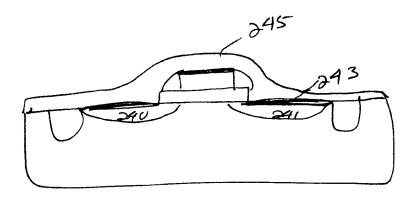


Fig 2(K)

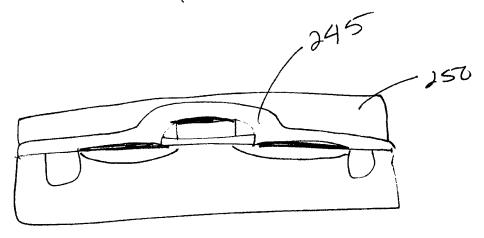
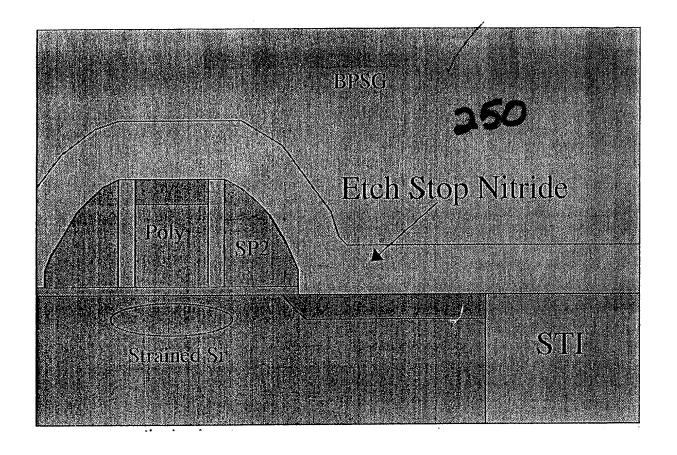


Fig &a(1)

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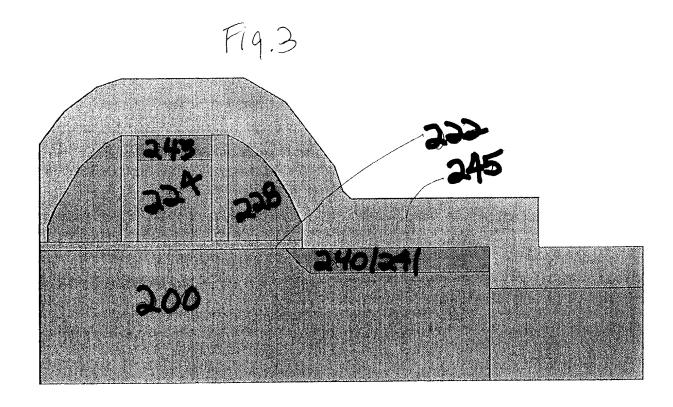


Fig. 4

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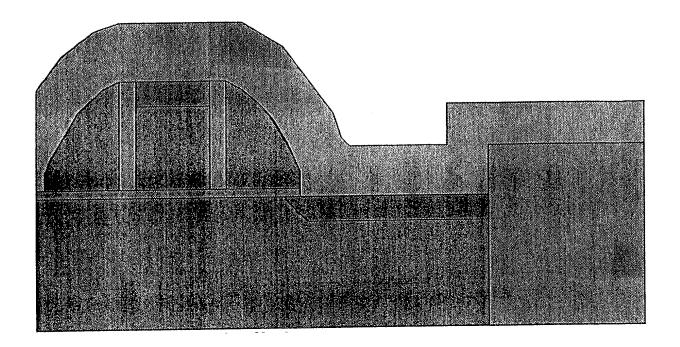
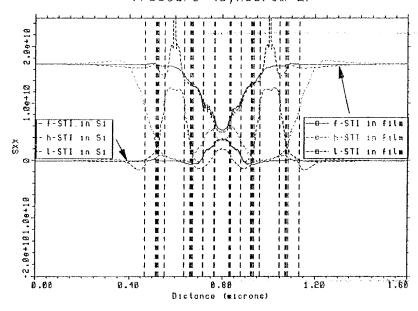


Fig 5

Stress Sxx vs. hight of STI-oxide

In Si cut at y=+0.01um and in film y=-0.01um Pressure (dynes/cm²)



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Stress Sxx vs. hight of STI-oxide

In Si cut at y= + 0.01um

Pressure (dynes/cm^2)

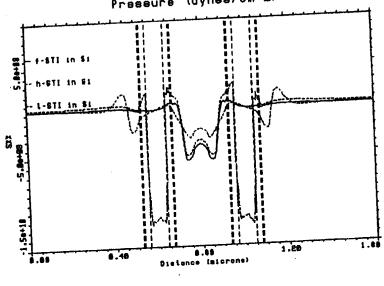
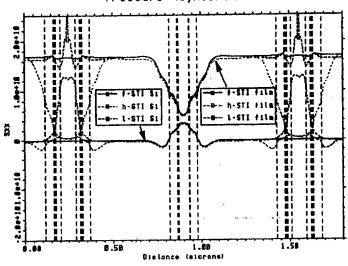


Fig .7

Stress Sxx vs. hight of STI-oxide w/ large PC-STI distance in Si cut at y=-0.01um and in film y=0.01um

Pressure (dynes/cm²2)



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Fig. 8